

isc N-Channel MOSFET Transistor

NDFP03N150C

• FEATURES

- · High breakdown voltage
- · Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

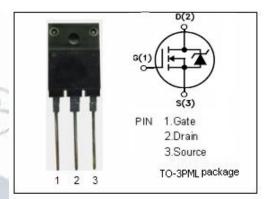
- · High speed power switching
- Switching regulator, DC-DC converter

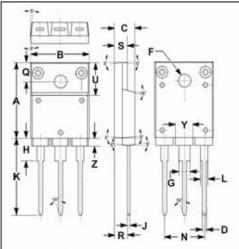


| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|--|---------|--------------|
| V _{DSS} | Drain-Source Voltage | 1500 | V |
| V _{GS} | Gate-Source Voltage | ±30 | V |
| I _D | Drain Current-Continuous | 2.5 | A |
| I _{DM} | Drain Current-Single Pulsed | 5 | А |
| P _D | Total Dissipation @T _C =25℃ | 50 | W |
| Tj | Max. Operating Junction Temperature | 150 | $^{\circ}$ C |
| T _{stg} | Storage Temperature | -55~150 | $^{\circ}$ C |
| | 77 | | |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|-----------|------------------------------------|-----|------|
| Rth(ch-c) | Channel-to-case thermal resistance | 2.5 | °C/W |





| | mm | | |
|-----|-------|-------|--|
| DIM | MIN | MAX | |
| Α | 19.90 | 20.10 | |
| В | 15.75 | 16.10 | |
| C | 5.50 | 5.70 | |
| D | 0.90 | 1.10 | |
| F | 3.30 | 3.50 | |
| G | 2.90 | 3.20 | |
| Н | 5.90 | 6.10 | |
| J | 0.595 | 0.70 | |
| K | 21.10 | 22.50 | |
| L | 1.90 | 2.25 | |
| N | 10.80 | 11.00 | |
| 0 | 4.90 | 5.10 | |
| R | 3.75 | 3.95 | |
| S | 3.20 | 3.60 | |
| U | 9.90 | 10.10 | |
| Y | 4.20 | 4.90 | |
| Z | 1.90 | 2.10 | |

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | ТҮР | МАХ | UNIT |
|---------------------|--------------------------------|---|------|-----|------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V; ID =10mA | 1500 | | | V |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} ; ID =1mA | 3 | | 5 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} =15V ^{NOTE} ; I _D =1A | | | 10 | Ω |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} = ±30V;V _{DS} =0V | | | ±100 | nA |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} =1200V; V _{GS} = 0V | | | 1 | mA |
| V _{SD} | Diode forward voltage | I _S =2A; V _{GS} = 0V | | | 1.5 | V |

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